

**300V NPN HIGH VOLTAGE TRANSISTOR IN SOT223**
**Description**

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

**Features**

- $BV_{CEO} > 300V$
- $I_C = 500mA$  High Collector Current
- 2W Power Dissipation
- Low Saturation Voltage  $V_{CE(SAT)} < 500mV @ 20mA$
- Complementary PNP Type: DZTA92
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

**Mechanical Data**

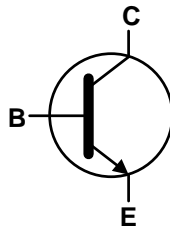
- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.112 grams (Approximate)

**Applications**

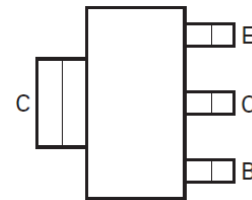
- Switch-Mode Power Supplies (SMPS)
- Video Output Stages
- Motor Driver



Top View



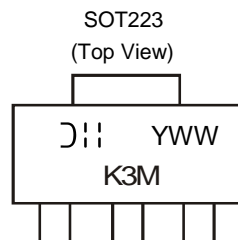
Device Symbol


 Top View  
Pin-Out

**Ordering Information** (Note 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DZTA42Q-13	Automotive	K3M	13	12	2,500

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to <https://www.diodes.com/quality/>.
  5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**


- K3M = Product Type Marking Code
- D = Manufacturer's Code Marking
- YWW = Date Code Marking
- Y = Last Digit of Year (ex: 8 = 2018)
- WW = Week Code (01 to 53)

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	300	V
Collector-Emitter Voltage	V <sub>CEO</sub>	300	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current	I <sub>C</sub>	500	mA
Base Current	I <sub>B</sub>	100	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

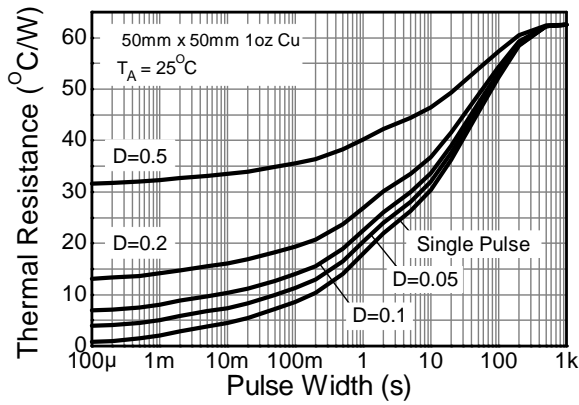
Characteristic	Symbol	Value	Unit
Power Dissipation	P <sub>D</sub>	(Note 6)	2
		(Note 7)	1
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	(Note 6)	62
		(Note 7)	125
Thermal Resistance, Junction to Leads	R <sub>θJL</sub>	19.4	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

**ESD Ratings** (Note 9)

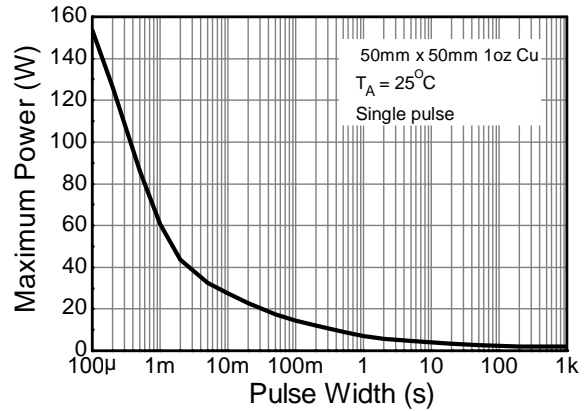
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the collector lead on 50mm x 50mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  7. Same as note (6), except mounted on minimum recommended pad (MRP) layout.
  8. Thermal resistance from junction to solder-point (at the end of the collector lead).
  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

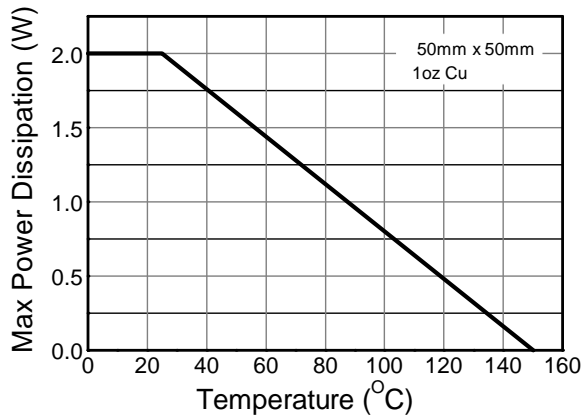
**Thermal Characteristics and Derating Information**



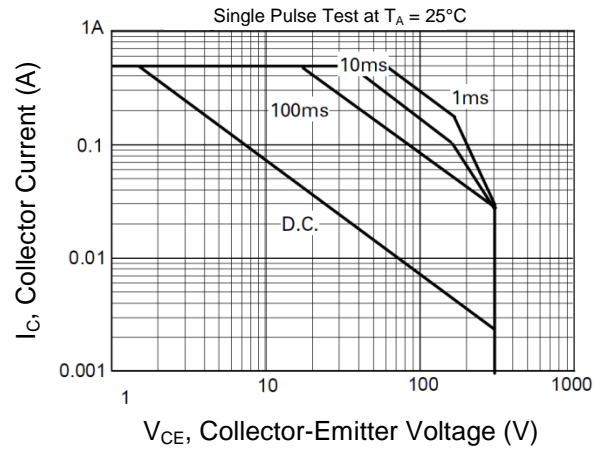
**Transient Thermal Impedance**



**Pulse Power Dissipation**



**Derating Curve**



**Safe Operating Area**

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	300	—	—	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	300	—	—	V	I <sub>C</sub> = 1mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	—	—	V	I <sub>E</sub> = 100μA
Collector-Base Cut-off Current	I <sub>CBO</sub>	—	—	0.1	μA	V <sub>CB</sub> = 200V
Emitter-Base Cut-off Current	I <sub>EBO</sub>	—	—	0.1	μA	V <sub>EB</sub> = 6V
<b>ON CHARACTERISTICS (Note 10)</b>						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	—	0.5	V	I <sub>C</sub> = 20mA, I <sub>B</sub> = 2mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	—	0.9	V	I <sub>C</sub> = 20mA, I <sub>B</sub> = 2mA
Static Forward Current Transfer Ratio	h <sub>FE</sub>	25	—	—	—	I <sub>C</sub> = 1mA, V <sub>CE</sub> = 10V
		40	—	—		I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V
		40	—	—		I <sub>C</sub> = 30mA, V <sub>CE</sub> = 10V
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Transition Frequency	f <sub>T</sub>	50	—	—	MHz	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 20V f = 100MHz
Output Capacitance	C <sub>OBO</sub>	—	—	3	pF	V <sub>CB</sub> = 20V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

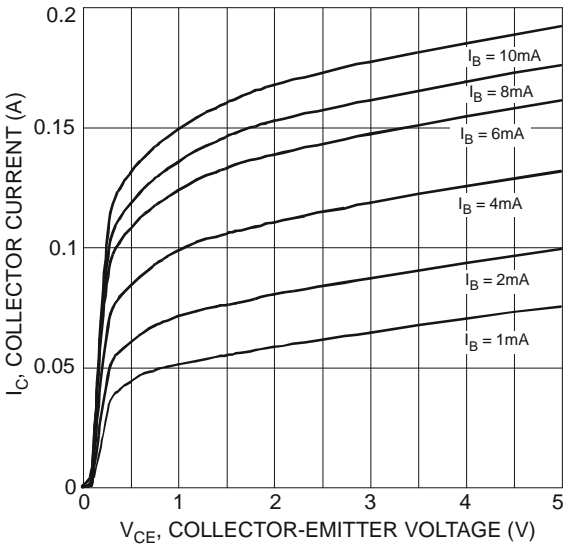


Figure 1 Typical Collector Current vs. Collector-Emitter Voltage

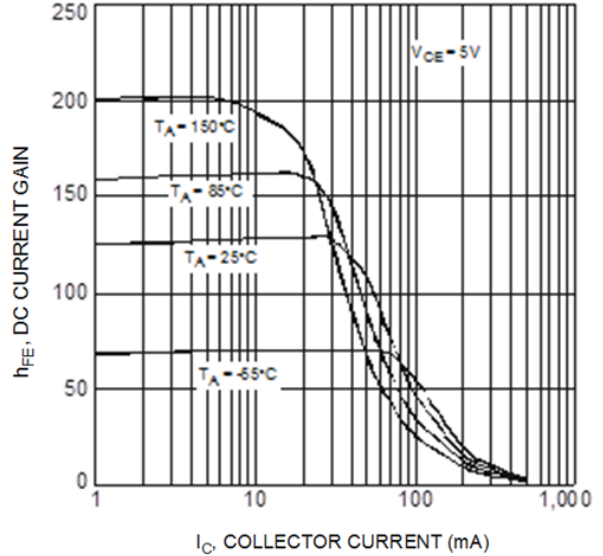


Figure 2 Typical DC Current Gain vs. Collector Current

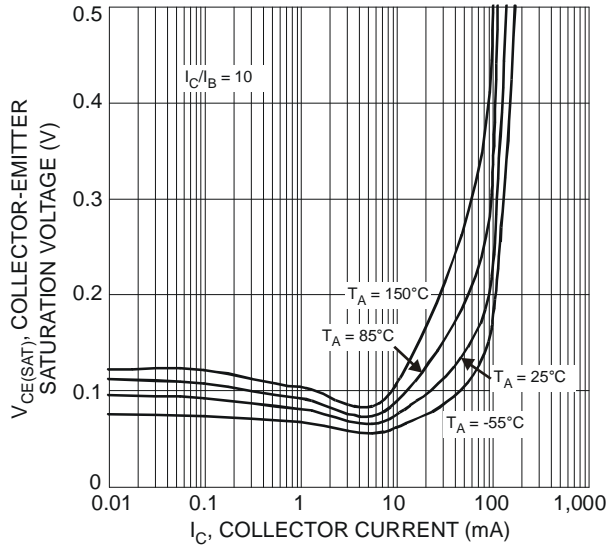


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

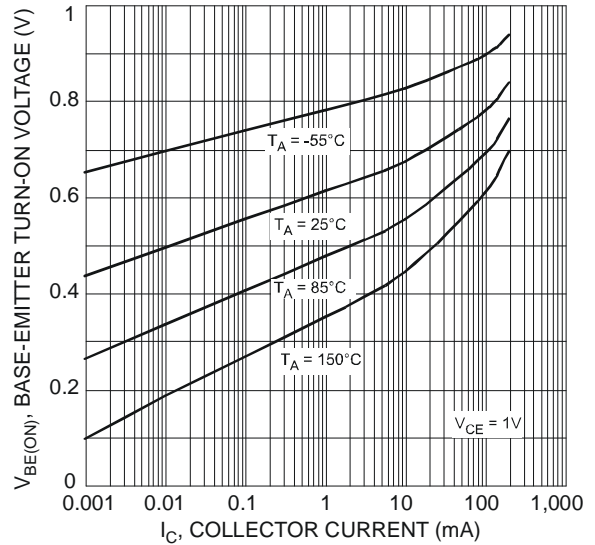


Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

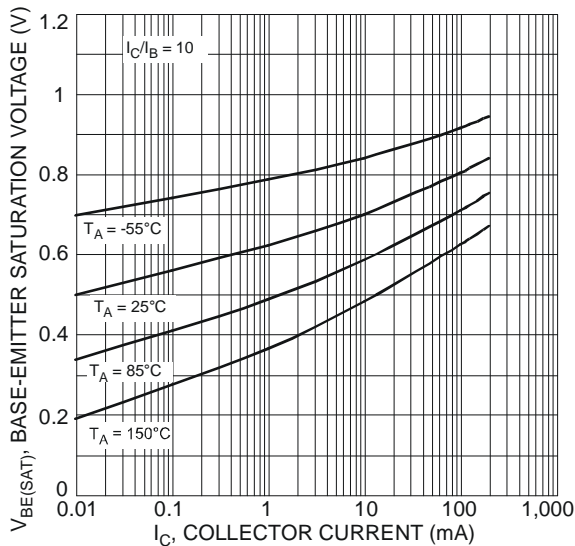


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

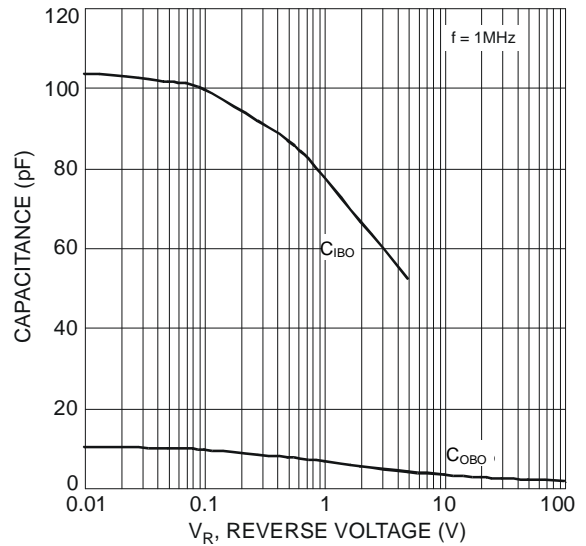


Figure 6 Typical Capacitance Characteristics

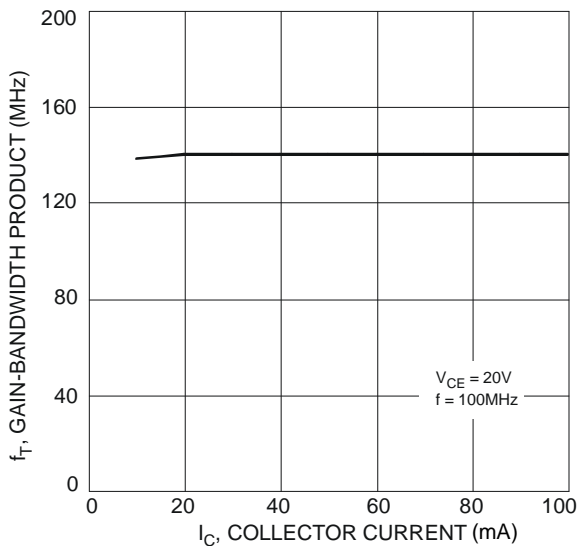
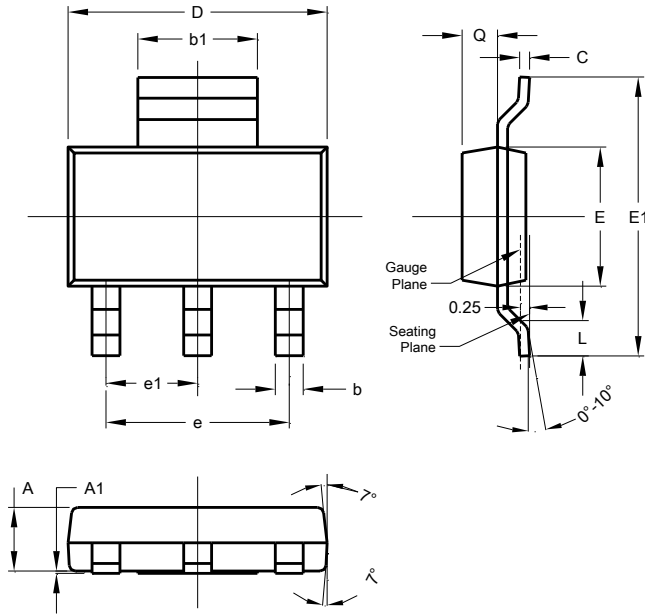


Figure 7 Typical Gain-Bandwidth Product vs. Collector Current

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT223**

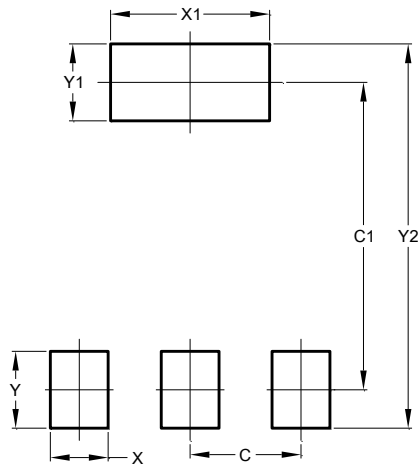


SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT223**



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.

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